

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74VCX162835FT**LOW-VOLTAGE 18-BIT UNIVERSAL BUS DRIVER
WITH 3.6 V TOLERANT INPUTS AND OUTPUTS**

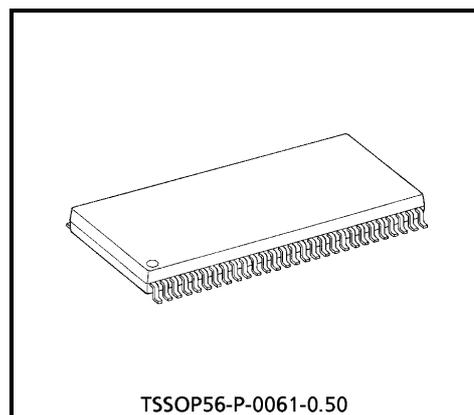
The TC74VCX162835FT is a high performance CMOS 18-bit UNIVERSAL BUS DRIVER. Designed for use in 1.8, 2.5 or 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to 3.6V.

Data flow from A to Y is controlled by the output-enable (\overline{OE}) input. The device operates in the transparent mode when the latch-enable (LE) input is high. When LE is low, the A data is latched if the clock (CLK) input is held at a high or low logic level. If LE is low, the A data is stored in the latch / flip-flop on the low-to-high transition of CLK. When \overline{OE} is high, the outputs are in the high-impedance state.

The 26- Ω series resistor helps reducing output overshoot and undershoot without external resistor.

All inputs are equipped with protection circuits against static discharge.



TSSOP56-P-0061-0.50

Weight : 0.25 g (Typ.)

FEATURES

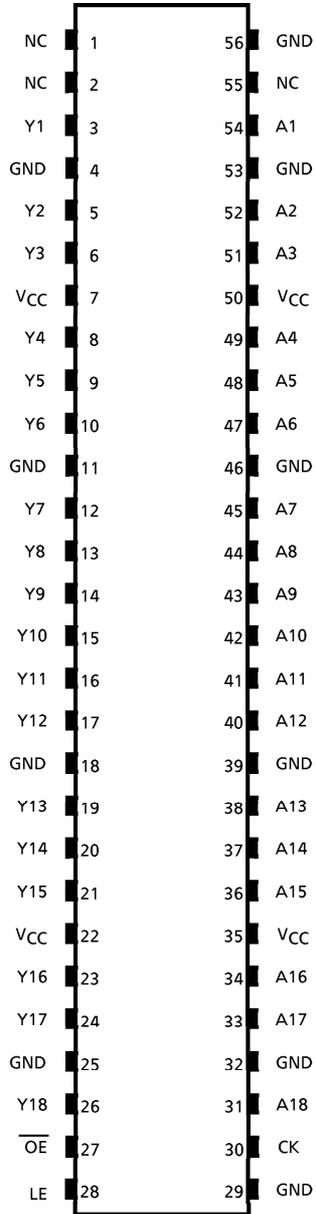
- 26- Ω Series Resistors on Outputs.
- Low Voltage Operation : $V_{CC} = 1.8\sim 3.6\text{ V}$
- High Speed Operation : $t_{pd} = 3.9\text{ ns (max.) at } V_{CC} = 3.0\sim 3.6\text{ V}$
 : $t_{pd} = 5.0\text{ ns (max.) at } V_{CC} = 2.3\sim 2.7\text{ V}$
 : $t_{pd} = 9.8\text{ ns (max.) at } V_{CC} = 1.8\text{ V}$
- 3.6 V Tolerant inputs and outputs.
- Output Current : $I_{OH}/I_{OL} = \pm 12\text{ mA (min.) at } V_{CC} = 3.0\text{ V}$
 : $I_{OH}/I_{OL} = \pm 8\text{ mA (min.) at } V_{CC} = 2.3\text{ V}$
 : $I_{OH}/I_{OL} = \pm 4\text{ mA (min.) at } V_{CC} = 1.8\text{ V}$
- Latch-up Performance : $\pm 300\text{ mA}$
- ESD Performance : Human Body Model $> \pm 2000\text{ V}$
 : Machine Model $> \pm 200\text{ V}$
- Package : TSSOP
 (Thin Shrink Small Outline Package)
- Power Down Protection is provided on all inputs and outputs.
- Supports live insertion / withdrawal (Note 1)

(Note 1) : To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

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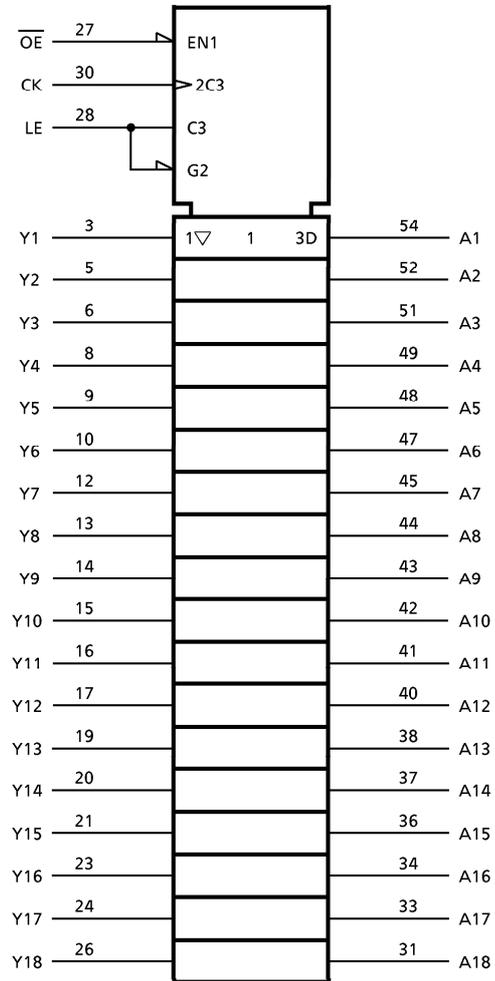
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PIN ASSIGNMENT



(TOP VIEW)

SYMBOL

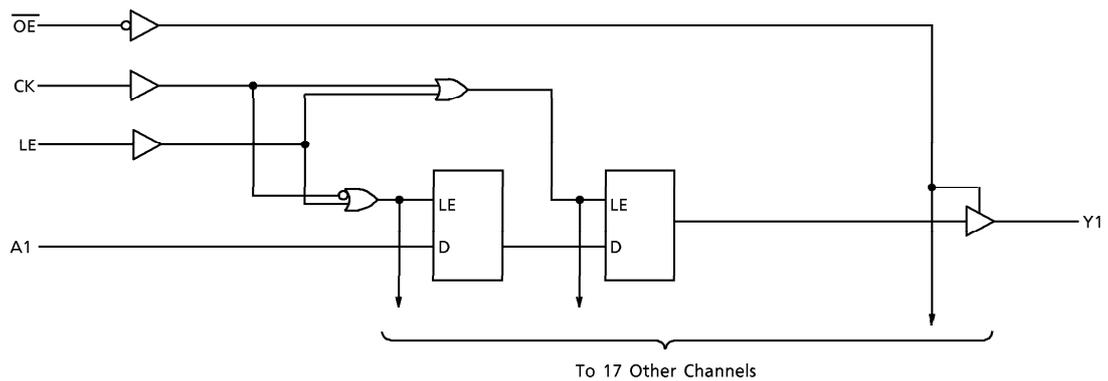


TRUTH TABLE

INPUTS				OUTPUTS
\overline{OE}	LE	CK	A	Y
H	X	X	X	Z
L	H	X	L	L
L	H	X	H	H
L	L	\uparrow	L	L
L	L	\downarrow	H	H
L	L	H	X	Y0 *
L	L	L	X	Y0 *

* Output level before the indicated steady-state input conditions were established, provided that CK was high or low before LE went low.

SYSTEM DIAGRAM



MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Power Supply Voltage	V_{CC}	-0.5~4.6	V
DC Input Voltage	V_{IN}	-0.5~4.6	V
DC Output Voltage	V_{OUT}	-0.5~4.6 (Note 2)	V
		-0.5~ $V_{CC} + 0.5$ (Note 3)	
Input Diode Current	I_{IK}	-50	mA
Output Diode Current	I_{OK}	± 50 (Note 4)	mA
DC Output Current	I_{OUT}	± 50	mA
Power Dissipation	P_D	400	mW
DC V_{CC} /Ground Current Per Supply Pin	I_{CC}/I_{GND}	± 100	mA
Storage Temperature	T_{stg}	-65~150	$^{\circ}\text{C}$

(Note 2) : Off-State

(Note 3) : High or Low State. I_{OUT} absolute maximum rating must be observed.

(Note 4) : $V_{OUT} < \text{GND}$, $V_{OUT} > V_{CC}$

RECOMMENDED OPERATING RANGE

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	1.8~3.6	V
		1.2~3.6 (Note 5)	
Input Voltage	V_{IN}	-0.3~3.6	V
Output Voltage	$V_{I/O}$	0~3.6 (Note 6)	V
		0~ V_{CC} (Note 7)	
Output Current	I_{OH}/I_{OL}	± 12 (Note 8)	mA
		± 8 (Note 9)	
		± 4 (Note 10)	
Operating Temperature	T_{opr}	-40~85	$^{\circ}\text{C}$
Input Rise And Fall Time	dt/dv	0~10 (Note 11)	ns/V

(Note 5) : Data Retention Only

(Note 6) : Off-State

(Note 7) : High or Low State

(Note 8) : $V_{CC} = 3.0\sim 3.6\text{ V}$

(Note 9) : $V_{CC} = 2.3\sim 2.7\text{ V}$

(Note 10) : $V_{CC} = 1.8\text{ V}$

(Note 11) : $V_{IN} = 0.8\sim 2.0\text{ V}$, $V_{CC} = 3.0\text{ V}$

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = -40~85°C, 2.7 V < VCC ≤ 3.6 V)

PARAMETER		SYMBOL	TEST CONDITION	VCC (V)	MIN.	MAX.	UNIT	
Input Voltage	"H" Level	V _{IH}		2.7~3.6	2.0	—	V	
	"L" Level	V _{IL}		2.7~3.6	—	0.8		
Output Voltage	"H" Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.7~3.6	V _{CC} - 0.2	—	V
				I _{OH} = -6 mA	2.7	2.2	—	
				I _{OH} = -8 mA	3.0	2.4	—	
				I _{OH} = -12 mA	3.0	2.2	—	
	"L" Level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.7~3.6	—	0.2	
				I _{OL} = 6 mA	2.7	—	0.4	
				I _{OL} = 8 mA	3.0	—	0.55	
				I _{OL} = 12 mA	3.0	—	0.8	
Input Leakage Current		I _{IN}	V _{IN} = 0~3.6 V	2.7~3.6	—	± 5.0	μA	
3-State Output Off-State Current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V	2.7~3.6	—	± 10.0	μA	
Power Off Leakage Current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V	0	—	10.0	μA	
Quiescent Supply Current		I _{CC}	V _{IN} = V _{CC} or GND	2.7~3.6	—	20.0	μA	
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V	2.7~3.6	—	± 20.0		
Increase In I _{CC} Per Input		ΔI _{CC}	V _{IH} = V _{CC} - 0.6 V	2.7~3.6	—	750	μA	

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = -40~85°C, 2.3 V ≤ VCC ≤ 2.7 V)

PARAMETER		SYMBOL	TEST CONDITION	VCC (V)	MIN.	MAX.	UNIT	
Input Voltage	"H" Level	V _{IH}		2.3~2.7	1.6	—	V	
	"L" Level	V _{IL}		2.3~2.7	—	0.7		
Output Voltage	"H" Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	—	V
				I _{OH} = -4 mA	2.3	2.0	—	
				I _{OH} = -6 mA	2.3	1.8	—	
				I _{OH} = -8 mA	2.3	1.7	—	
	"L" Level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.3~2.7	—	0.2	
				I _{OL} = 6 mA	2.3	—	0.4	
				I _{OL} = 8 mA	2.3	—	0.6	
Input Leakage Current		I _{IN}	V _{IN} = 0~3.6 V	2.3~2.7	—	± 5.0	μA	
3-State Output Off-State Current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V	2.3~2.7	—	± 10.0	μA	
Power Off Leakage Current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V	0	—	10.0	μA	
Quiescent Supply Current		I _{CC}	V _{IN} = V _{CC} or GND	2.3~2.7	—	20.0	μA	
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V	2.3~2.7	—	± 20.0		

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = -40~85°C, 1.8 V ≤ VCC < 2.3 V)

PARAMETER		SYMBOL	TEST CONDITION		VCC (V)	MIN.	MAX.	UNIT
					1.8~2.3			
Input Voltage	"H" Level	V _{IH}			1.8~2.3	0.7 × V _{CC}	—	V
	"L" Level	V _{IL}			1.8~2.3	—	0.2 × V _{CC}	
Output Voltage	"H" Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	—	V
				I _{OH} = -4 mA	1.8	1.4	—	
	"L" Level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	1.8	—	0.2	
				I _{OL} = 4 mA	1.8	—	0.3	
Input Leakage Current		I _{IN}	V _{IN} = 0~3.6 V		1.8	—	± 5.0	μA
3-State Output Off-State Current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V		1.8	—	± 10.0	μA
Power Off Leakage Current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent Supply Current		I _{CC}	V _{IN} = V _{CC} or GND		1.8	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		1.8	—	± 20.0	

AC characteristics (Ta = -40~85°C, Input tr = tf = 2.0 ns, CL = 30 pF, RL = 500 Ω)

PARAMETER	SYMBOL	TEST CONDITION	VCC (V)	MIN.	MAX.	UNIT
Maximum Clock Frequency	fMAX	(Fig.1, 2)	1.8	100	—	MHz
			2.5 ± 0.2	200	—	
			3.3 ± 0.3	250	—	
Propagation Delay Time (An-Yn)	tpLH tpHL	(Fig.1, 2)	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	5.0	
			3.3 ± 0.3	0.6	3.9	
Propagation Delay Time (CK-Yn)	tpLH tpHL	(Fig.1, 3)	1.8	2.0	9.2	ns
			2.5 ± 0.2	1.5	5.2	
			3.3 ± 0.3	1.4	4.2	
Propagation Delay Time (LE-Yn)	tpLH tpHL	(Fig.1, 4)	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	5.8	
			3.3 ± 0.3	0.6	4.7	
Output Enable Time	tpZL tpZH	(Fig.1, 5)	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	5.9	
			3.3 ± 0.3	0.6	4.3	
Output Disable Time	tpLZ tpHZ	(Fig.1, 5)	1.8	1.5	7.9	ns
			2.5 ± 0.2	0.8	4.7	
			3.3 ± 0.3	0.6	4.2	
Minimum Pulse Width	tw (H) tw (L)	(Fig.1, 3, 4)	1.8	4.0	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum Set-up Time (An-CK, An-LE)	ts	(Fig.1, 3, 4)	1.8	2.5	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum Hold Time (An-CK, An-LE)	th	(Fig.1, 3, 4)	1.8	1.0	—	ns
			2.5 ± 0.2	0.7	—	
			3.3 ± 0.3	0.7	—	
Output to Output Skew	tosLH tosHL	(Note 12)	1.8	—	0.5	ns
			2.5 ± 0.2	—	0.5	
			3.3 ± 0.3	—	0.5	

(Note 12) : Parameter guaranteed by design.

$$(tosLH = |tpLHm - tpLHn|, tosHL = |tpHLm - tpHLn|)$$

AC characteristics (Ta = 0~85°C, Input $t_r = t_f = 2.0$ ns, $C_L = 0$ pF, $R_L = 500$ Ω)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	MIN.	MAX.	UNIT
Propagation Delay Time (An-Yn) (Note 13)	t_{pLH} t_{pHL}	(Fig.1, 2)	3.3 ± 0.15	0.9	2.0	ns
Propagation Delay Time (CK-Yn) (Note 13)	t_{pLH} t_{pHL}	(Fig.1, 3)	3.3 ± 0.15	1.4	2.9	ns
Propagation Delay Time (LE-Yn) (Note 13)	t_{pLH} t_{pHL}	(Fig.1, 4)	3.3 ± 0.15	0.7	3.4	ns
Output Enable Time (Note 13)	t_{pZL} t_{pZH}	(Fig.1, 5)	3.3 ± 0.15	0.7	3.0	ns
Output Disable Time (Note 13)	t_{pLZ} t_{pHZ}	(Fig.1, 5)	3.3 ± 0.15	0.7	2.9	ns
Minimum Set-up Time (An-CK, An-LE) (Note 13)	t_s	(Fig.1, 3, 4)	3.3 ± 0.15	1.5	—	ns
Minimum Hold Time (An-CK, An-LE) (Note 13)	t_h	(Fig.1, 3, 4)	3.3 ± 0.15	0.7	—	ns

(Note 13) : TOSHIBA SPICE simulation data.

AC characteristics (Ta = 0~85°C, Input $t_r = t_f = 2.0$ ns, $C_L = 50$ pF, $R_L = 500$ Ω)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	MIN.	MAX.	UNIT
Propagation Delay Time (An-Yn)	t_{pLH} t_{pHL}	(Fig.1, 2)	3.3 ± 0.15	1.0	4.2	ns
Propagation Delay Time (CK-Yn)	t_{pLH} t_{pHL}	(Fig.1, 3)	3.3 ± 0.15	1.9	4.5	ns
Propagation Delay Time (LE-Yn)	t_{pLH} t_{pHL}	(Fig.1, 4)	3.3 ± 0.15	1.0	5.0	ns
Output Enable Time	t_{pZL} t_{pZH}	(Fig.1, 5)	3.3 ± 0.15	1.0	4.6	ns
Output Disable Time	t_{pLZ} t_{pHZ}	(Fig.1, 5)	3.3 ± 0.15	1.0	4.5	ns
Minimum Set-up Time (An-CK, An-LE)	t_s	(Fig.1, 3, 4)	3.3 ± 0.15	1.5	—	ns
Minimum Hold Time (An-CK, An-LE)	t_h	(Fig.1, 3, 4)	3.3 ± 0.15	0.7	—	ns

Dynamic switching characteristics (Ta = 25°C, Input tr = tf = 2.0 ns, CL = 30 pF)

PARAMETER	SYMBOL	TEST CONDITION	VCC (V)	TYP.	UNIT
Quiet Output Maximum Dynamic VOL	VOLP	V _{IH} = 1.8 V, V _{IL} = 0 V (Note 14)	1.8	0.25	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note 14)	2.5	0.35	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note 14)	3.3	0.45	
Quiet Output Minimum Dynamic VOL	VOLV	V _{IH} = 1.8 V, V _{IL} = 0 V (Note 14)	1.8	-0.25	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note 14)	2.5	-0.35	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note 14)	3.3	-0.45	
Quiet Output Minimum Dynamic VOH	VOHV	V _{IH} = 1.8 V, V _{IL} = 0 V (Note 14)	1.8	1.35	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note 14)	2.5	1.85	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note 14)	3.3	2.45	

(Note 14) : Parameter guaranteed by design.

Capacitive characteristics (Ta = 25°C)

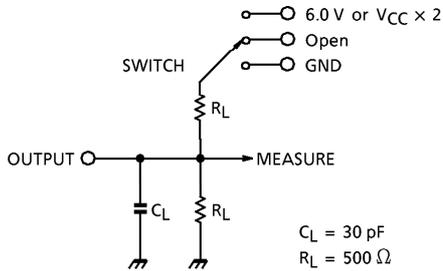
PARAMETER	SYMBOL	TEST CONDITION	VCC (V)	TYP.	UNIT
Input Capacitance	C _{IN}		1.8, 2.5, 3.3	6	pF
Output Capacitance	C _{I/O}		1.8, 2.5, 3.3	7	pF
Power Dissipation Capacitance	C _{PD}	f _{IN} = 10 MHz (Note 15)	1.8, 2.5, 3.3	20	pF

(Note 15) : C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 18 \text{ (per bit)}$$

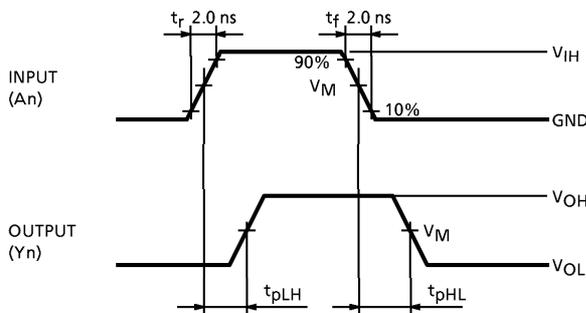
Fig.1 Test circuit



PARAMETER	SWITCH
t_{pLH}, t_{pHL}	Open
t_{pLZ}, t_{pZL}	6.0 V @ $V_{CC} = 3.3 \pm 0.3$ V $V_{CC} \times 2$ @ $V_{CC} = 2.5 \pm 0.2$ V @ $V_{CC} = 1.8$ V
t_{pHZ}, t_{pZH}	GND

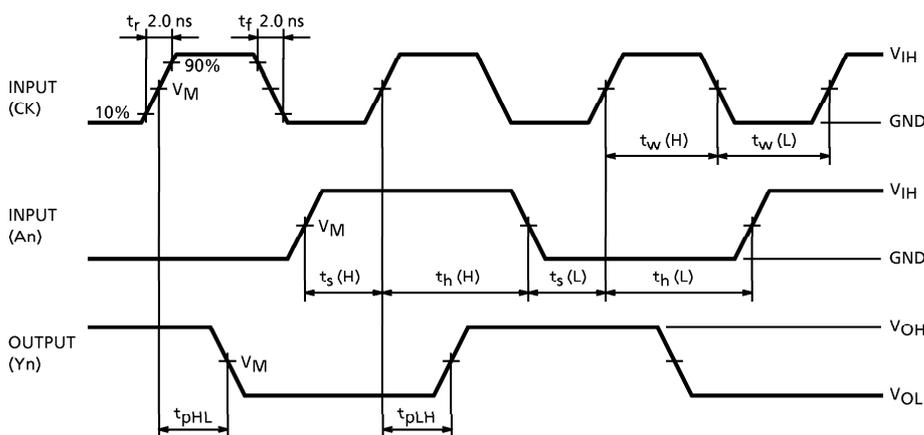
AC WAVEFORM

Fig.2 t_{pLH}, t_{pHL}



SYMBOL	V_{CC}		
	3.3 ± 0.3 V	2.5 ± 0.2 V	1.8 V
V_{IH}	2.7 V	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC} / 2$	$V_{CC} / 2$
V_X	$V_{OL} + 0.3$ V	$V_{OL} + 0.15$ V	$V_{OL} + 0.15$ V
V_Y	$V_{OH} - 0.3$ V	$V_{OH} - 0.15$ V	$V_{OH} - 0.15$ V

Fig.3 $t_{pLH}, t_{pHL}, t_w, t_s, t_h$



IBIS CHARACTERISTICS (Typ.)

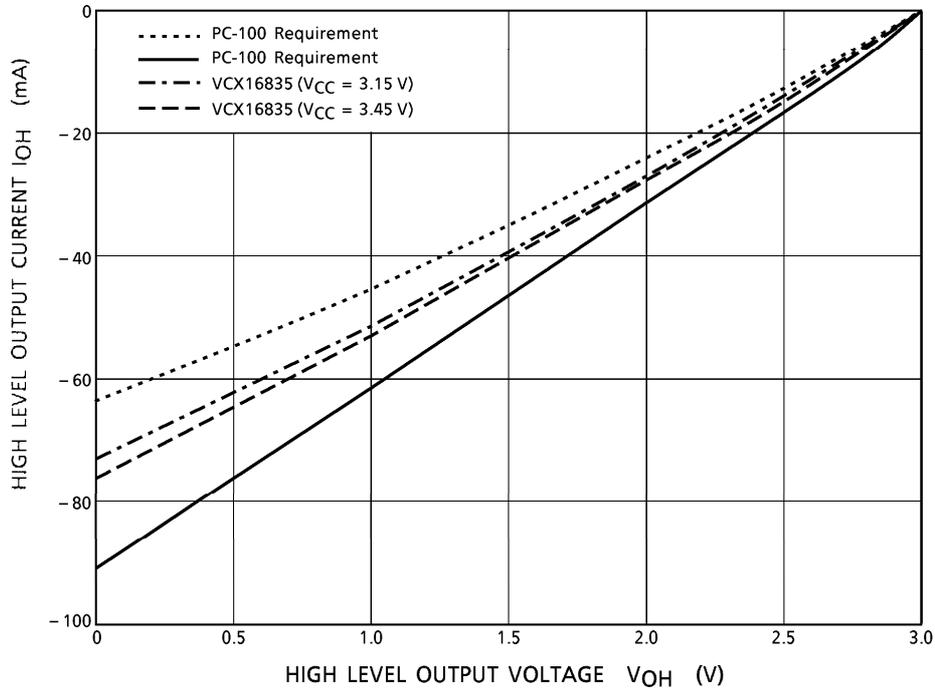


Fig.6 I/V Characteristics-Pullup

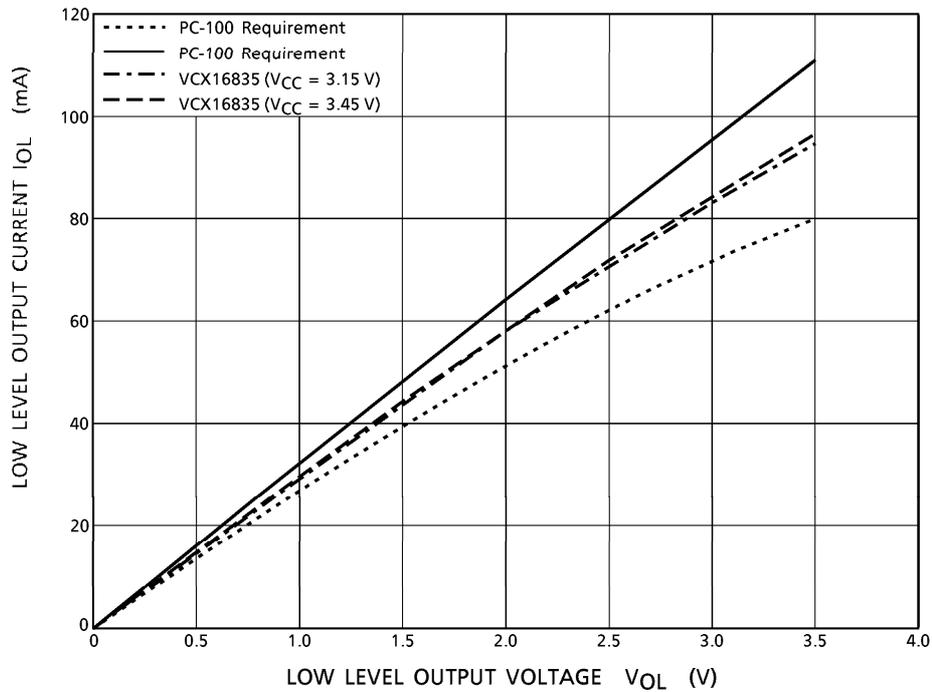
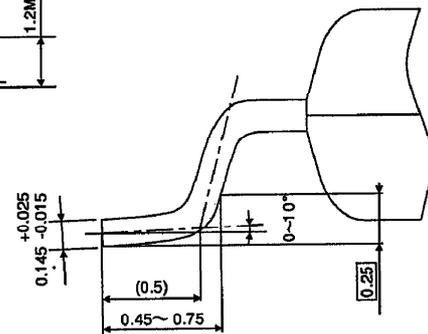
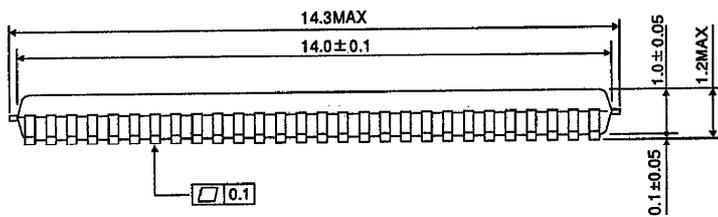
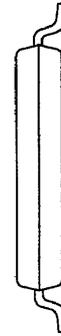
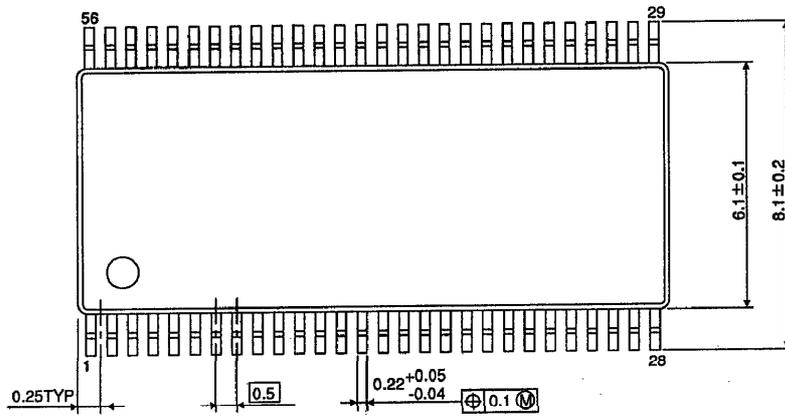


Fig.7 I/V Characteristics-Pulldown

OUTLINE DRAWING
TSSOP56-P-0061-0.50

Unit : mm



Weight : 0.25 g (Typ.)